Dual Series Switching Diodes

The BAV99WT1G is a smaller package, equivalent to the BAV99LT1G.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	100	Vdc
Forward Current	ΙF	215	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc
Repetitive Peak Reverse Voltage	V _{RRM}	100	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	I _{F(AV)}	715	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Non-Repetitive Peak Forward Current t = 1.0 μs t = 1.0 ms t = 1.0 s	I _{FSM}	2.0 1.0 0.5	А

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

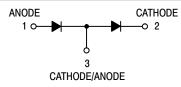


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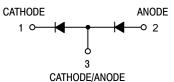
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SC-70 CASE 419

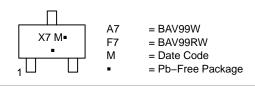


BAV99WT1 SC-70, CASE 419, STYLE 9



BAV99RWT1 SC-70, CASE 419, STYLE 10

MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
BAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVBAV99WT3G	SC-70 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

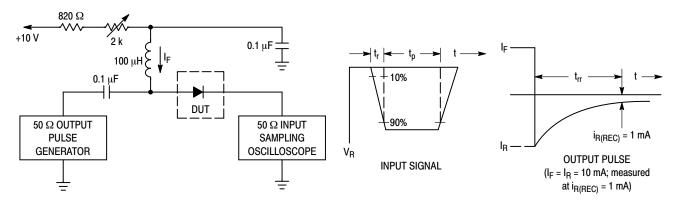
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	200 1.6	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	625	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Reverse Breakdown Voltage (I _(BR) = 100 μA)	V _(BR)	100	_	Vdc		
Reverse Voltage Leakage Current $(V_R = 100 \text{ Vdc})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 70 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I _R	- - -	1.0 30 50	μAdc		
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	_	1.5	pF		
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V _F	- - - -	715 855 1000 1250	mVdc		
Reverse Recovery Time (I _F = I _R = 10 mAdc, i _{R(REC)} = 1.0 mAdc) (Figure 1) R _L = 100 Ω	t _{rr}	_	6.0	ns		
Forward Recovery Voltage (I _F = 10 mA, t _r = 20 ns)	V _{FR}	-	1.75	V		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

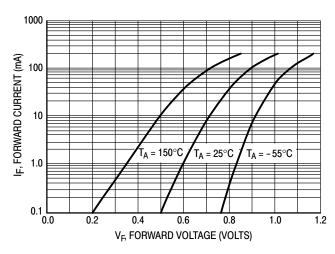


Notes: (a) A 2.0 k Ω variable resistor adjusted for a Forward Current (IF) of 10 mA.

- (b) Input pulse is adjusted so I_{R(peak)} is equal to 10 mA.
- (c) t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH DIODE



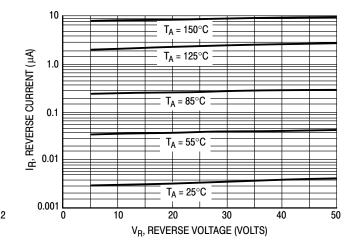


Figure 2. Forward Voltage

Figure 3. Leakage Current

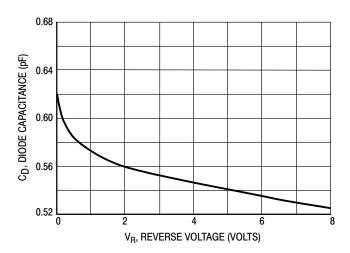
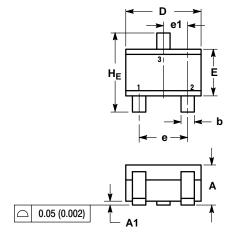
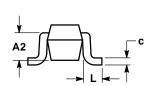


Figure 4. Capacitance

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 **ISSUE N**





- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF	=	
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

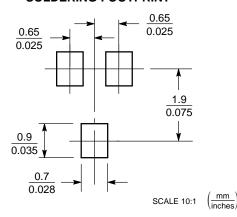
PIN 1 ANODE

3 CATHODE-ANODE

STYLE 10: PIN 1. CATHODE

2. ANODE 3. ANODE-CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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